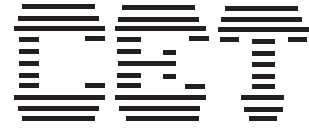


# CEDF640/CEUF640



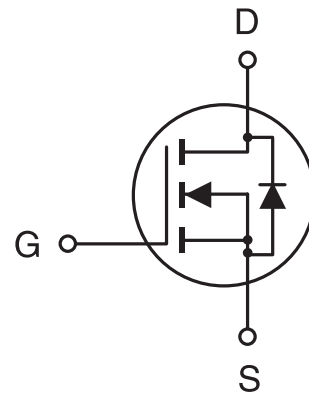
PRELIMINARY

## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

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- 200V , 18A ,  $R_{DS(ON)}=180m\Omega$  @  $V_{GS}=10V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- TO-251 & TO-252 package.



### ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	200	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous -Pulsed	I <sub>D</sub>	18	A
	I <sub>DM</sub>	72	A
Drain-Source Diode Forward Current	I <sub>S</sub>	18	A
Maximum Power Dissipation @T <sub>c</sub> =25°C Derate above 25°C	P <sub>D</sub>	50	W
		0.3	W/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 175	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	3	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	62.5	°C/W

# CEDF640/CEUF640

## ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	200			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V			25	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>ON CHARACTERISTICS<sup>a</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2		4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A			180	mΩ
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V	18			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 50V, I <sub>D</sub> = 11A	6.7			S
<b>DYNAMIC CHARACTERISTICS<sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz		1250	1700	pF
Output Capacitance	C <sub>OSS</sub>			188	250	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			60	80	pF
<b>SWITCHING CHARACTERISTICS<sup>b</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 100V, I <sub>D</sub> = 11A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 9.1Ω		16	30	ns
Rise Time	t <sub>r</sub>			70	105	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			50	85	ns
Fall time	t <sub>f</sub>			55	70	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 160V, I <sub>D</sub> = 18A, V <sub>GS</sub> = 10V		64	80	nC
Gate-Source Charge	Q <sub>gs</sub>			12		nC
Gate-Drain Charge	Q <sub>gd</sub>			37		nC

# CEDF640/CEUF640

## ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS<sup>a</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 18A$			1.5	V

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### Notes

- a. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

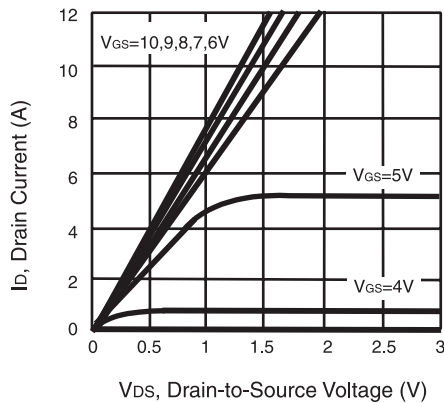


Figure 1. Output Characteristics

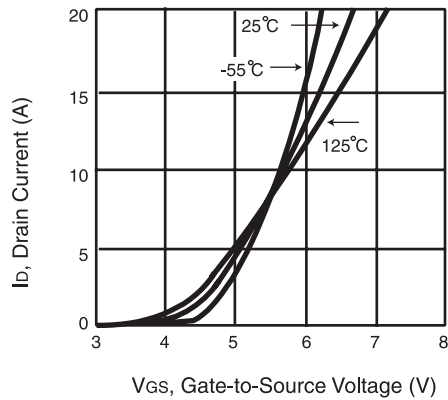


Figure 2. Transfer Characteristics

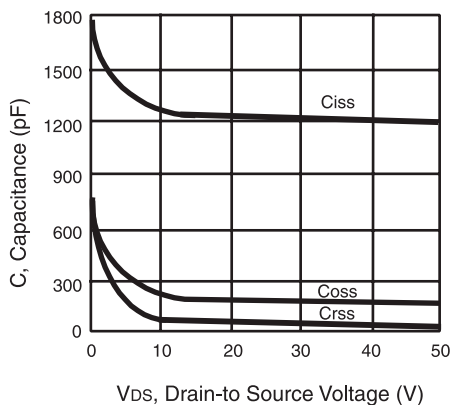


Figure 3. Capacitance

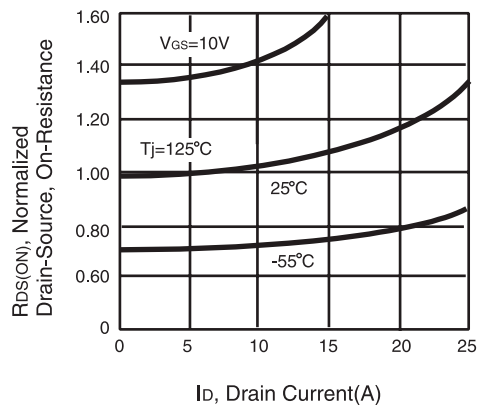
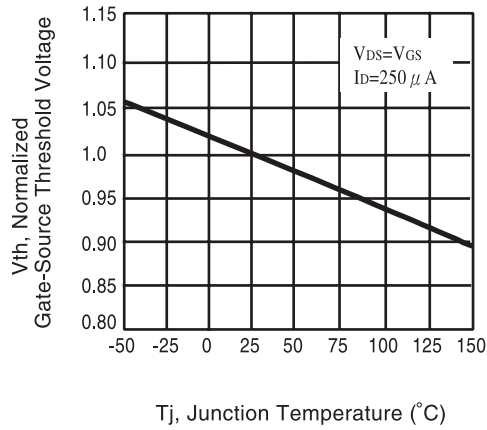


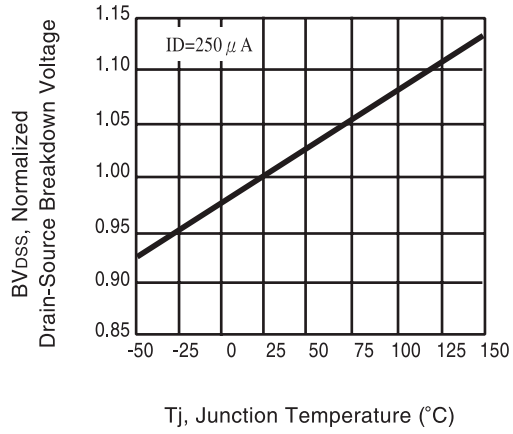
Figure 4. On-Resistance Variation with Drain Current and Temperature

# CEDF640/CEUF640

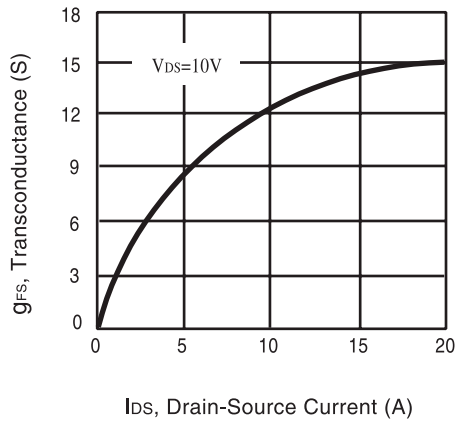
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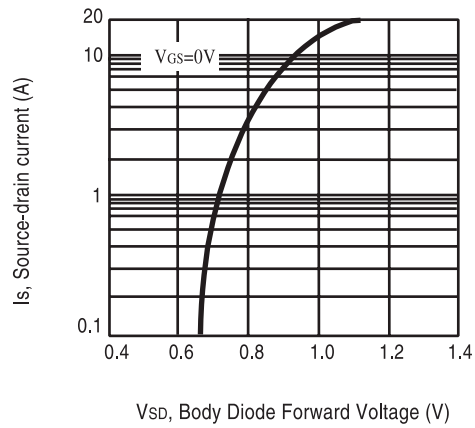
**Figure 5. Gate Threshold Variation with Temperature**



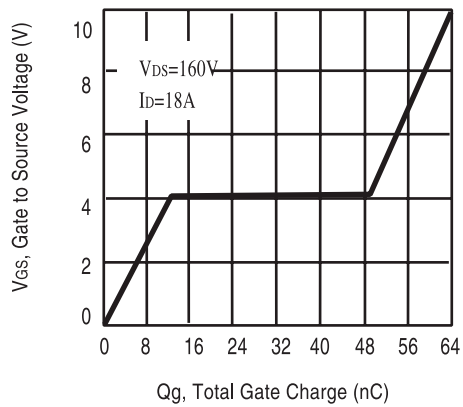
**Figure 6. Breakdown Voltage Variation with Temperature**



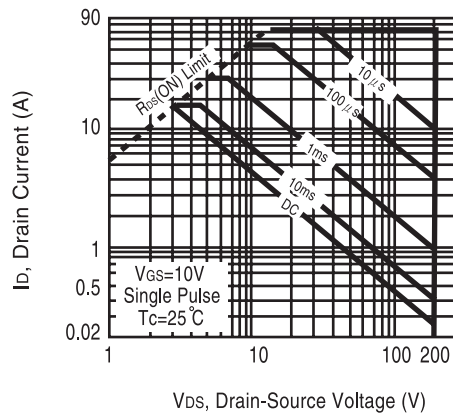
**Figure 7. Transconductance Variation with Drain Current**



**Figure 8. Body Diode Forward Voltage Variation with Source Current**



**Figure 9. Gate Charge**



**Figure 10. Maximum Safe Operating Area**

# CEDF640/CEUF640

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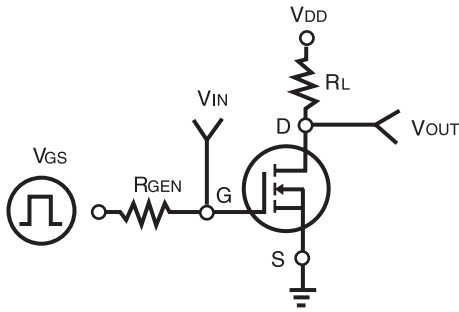


Figure 11. Switching Test Circuit

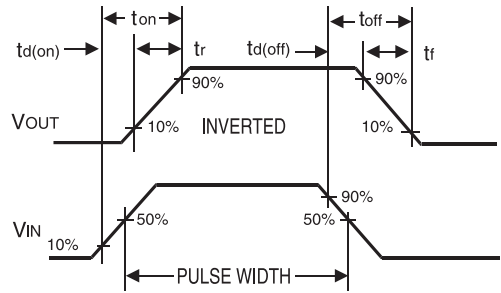


Figure 12. Switching Waveforms

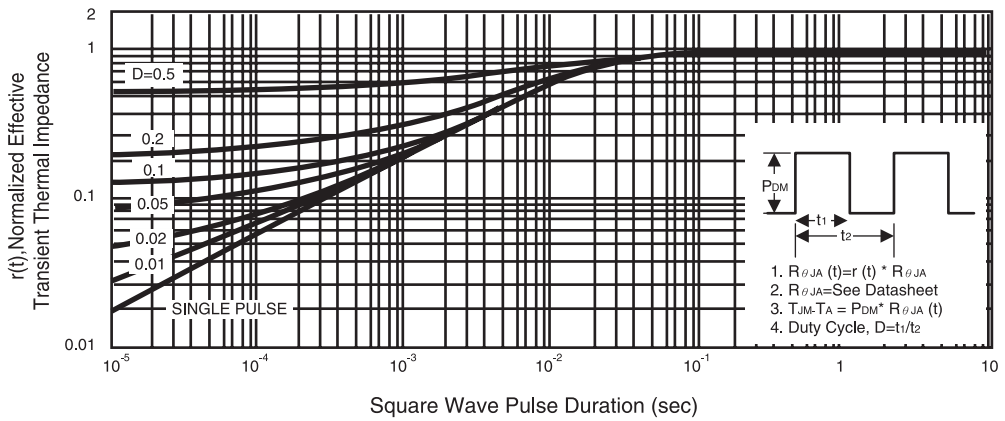


Figure 13. Normalized Thermal Transient Impedance Curve